

Valley polarization dynamics of photoinjected carriers at the band edge in room-temperature silicon studied by terahertz polarimetry

Ami M. Shirai*, Yuta Murotani, Tomohiro Fujimoto, Natsuki Kanda[‡], Jun Yoshinobu, and Ryusuke Matsunaga[†]

The Institute for Solid State Physics, The University of Tokyo, Kashiwa, Chiba 277-8581, Japan

*shirai-ami@issp.u-tokyo.ac.jp

[†]matsunaga@issp.u-tokyo.ac.jp

[‡]Present address: RIKEN Center for Advanced Photonics, RIKEN, 2-1 Hirosawa, Wako, Saitama 351-0198, Japan

Abstract

Sixfold-degenerate valleys in Si have attracted considerable attention for valleytronics application. Using optical pump-terahertz (THz) probe spectroscopy, we study the dynamics of valley polarization in bulk Si(001) at room temperature. Linearly polarized pump pulses excite electrons and holes with asymmetric distributions in momentum space, leading to in-plane anisotropic conductivity. By varying the polarization directions of the pump light relative to the in-plane crystalline axes, the valley polarization of electrons and the momentum asymmetry of holes are separately probed through observing the polarization rotation of THz pulses. We demonstrate that the valley relaxation time of electrons near the conduction band minimum exceeds 1.5 ps at room temperature, in good agreement with theoretically calculated intervalley phonon scattering with f-process. This work paves the way for Si-based room-temperature valleytronics.

Semiconductors that host degenerate valleys at the conduction band (CB) bottom or valence band (VB) top at different locations in momentum space have garnered attention for novel electronic device applications that exploit the valley degree of freedom [1-3]. While extensive studies on valleytronics have focused on two-dimensional (2D) honeycomb materials [4-8] over the past decade, valley-dependent transport has been investigated since the 1970s in the indirect-gap semiconductor Si, specifically in the inversion layer of metal-oxide-semiconductor field-effect transistors (MOSFETs) [1,9,10]. Si has sixfold valley degeneracy along Δ line in the CB. To enhance carrier mobility in Si MOSFETs, it is essential to lift the valley degeneracy through strain, which suppresses intervalley scattering [11,12]. The valley degeneracy and splitting in 2D quantum wells are also related to many-body physics and spin-based quantum computation [13,14]. The generation and controllability of valley polarization have also been investigated in AIAs [15,16] and diamond [17,18], materials with similar band structures.

For valley-related physics and applications, the relaxation time of valley polarization is a key parameter that must be determined experimentally. The valley polarization in Si can be generated by interband excitation with linearly polarized light due to differences in phonon-mediated transition rates for valleys that are parallel and perpendicular to the light polarization [19]. Historically, valley polarization dynamics in Si has been studied using cyclotron resonance spectroscopy [20,21], which is sensitive to differences in effective masses in highly asymmetric band dispersion [22]. However, the cyclotron resonance spectroscopy for Si has mainly been employed to study excitons at low temperatures with limited time resolution. For much faster time scales, recent time- and angle-resolved photoemission spectroscopy has enabled direct visualization of carrier dynamics in momentum space with resolutions of several tens of fs [23-25]. However, intervalley scattering dynamics has been observed only for hot electrons with large excess energies ($>$ a few hundred meV) from the valley bottom. Similarly, ultrafast carrier dynamics in Si has been studied in coherent phonon spectroscopy [26-29], extreme ultraviolet spectroscopy [30], and infrared spectroscopy [31], but these studies have concentrated on hot-carrier dynamics. To clarify valley-related transport for potential applications, observation of valley dynamics for carriers near the band edge at room temperature is required. This has evaded experimental clarification thus far, despite considerable interest in theoretical studies [32-36].

To reveal the carrier dynamics in Si, terahertz time-domain spectroscopy (THz-TDS) combined with optical pump pulses is a promising approach, as it can detect transient conductivity close to the DC limit with sub-100 fs time resolution [37-45]. When an electron population imbalance is created between the valleys along the [100] and [010] axes by optical pump pulses, the effective-mass anisotropy for each valley results in a transient anisotropic conductivity $\Delta\sigma \equiv$

$\sigma_{[100]} - \sigma_{[010]}$, which can be probed by polarization rotation of THz pulses. Recently, the accuracy of THz polarimetry combined with the pump-probe scheme has improved to better than 10 μrad [46], enabling sensitive detection of anisotropic conductivity, even for the small density of photoexcited carriers near the indirect band edges. Direct observation of anisotropic conductivity dynamics in Si will provide deeper insights into valley-related physics in multivalley semiconductors, offering potential for industrial applications.

In this study, we investigate valley polarization dynamics in bulk Si(001) at room temperature using near-infrared (NIR) pump-THz probe spectroscopy. The NIR pump pulses inject carriers into the band edge with asymmetric momentum distribution, and the anisotropic conductivity is probed by THz pulses. By selecting the polarization directions of the pump pulses relative to the in-plane crystalline axes, the contributions of CB valley polarization of electrons and VB momentum asymmetry of holes near the zone center can be separately probed. The effects of nonlinear photocurrent generation and phase shifts are carefully eliminated through 2D Fourier analysis. Our results reveal that the valley relaxation time exceeds 1.5 ps at room temperature, consistent with theoretical calculations of intervalley scattering.

Figure 1(a) illustrates the experimental setup. NIR pump pulses were generated by an optical parametric amplifier and second harmonic generation with a tunable wavelength between 900 and 1100 nm and a pulse duration of 200 fs. THz probe pulses were linearly polarized in the horizontal (x) direction before the sample. The transmitted THz pulses were detected by electro-optic (EO) sampling in a GaP(110) crystal using gate pulses with a 1030-nm wavelength and a 100-fs pulse duration. Two wire-grid polarizers (WGP1 and WGP2) were inserted into the THz beam path before EO sampling. When both WGPs were aligned parallel (upper configuration in Fig. 1(a)), the y -component of the THz field E_y was measured by EO sampling. In contrast, when only WGP1 was rotated by 45° (lower configuration), the EO sampling measured $(E_x + E_y)/2$. Thus, the two WGP configurations allowed the acquisition of both E_x and E_y . The probe and pump time delays, denoted as t_1 and t_2 , respectively, were independently scanned using mechanical stages. Additional details are provided in the Supplemental Material [47].

The sample was a 30 μm -thick, (001)-oriented undoped Si. All experiments were conducted at room temperature. Excitation by linearly polarized pump pulses for normal incidence breaks the fourfold symmetry of the (001) plane, resulting in in-plane anisotropic conductivity depending on the orientation of the pump polarization. This anisotropy was detected as a polarization rotation of the transmitted THz pulses due to linear birefringence and dichroism [61,62]. The pump and probe polarization directions used in this work are shown in Fig. 1(b). The incident THz pulses

were always x -polarized, while the pump polarization angle was switched between -45° and $+45^\circ$ from the x -direction. Additionally, two configurations for the in-plane crystal axis were switched by rotating the sample to discriminate the contributions of the CB and VB. This is because, not only the valley polarization of electrons, but also the asymmetric momentum distribution of holes is also induced by the linearly polarized pump as studied by coherent phonon spectroscopy [26-29,63-65]. In Configuration 1 (left panel), the (001)-oriented sample was mounted such that the $[100]$ axis was oriented by -45° relative to the x -direction in the xy -plane. The pump polarization along $[100]$ induces anisotropic conductivity $\Delta\sigma = \sigma_{[100]} - \sigma_{[010]}$ due to difference in electron populations between the $[100]$ and $[010]$ valleys. In the xy -coordinate system, the conductivity tensor has off-diagonal symmetric elements $\sigma_{xy} = \sigma_{yx} = \Delta\sigma/2$ [47], which rotate the probe polarization. We define this pump-induced polarization rotation ΔE_y as half the difference between the data measured with pump polarization at -45° ($[100]$) and $+45^\circ$ ($[010]$) to remove possible artifacts. In addition, to observe the contribution of the VB to the anisotropic conductivity, we used Configuration 2 (right), where the sample was set so that the pump light was polarized along the $[110]$ or $[\bar{1}10]$ directions. In this case, the in-plane valley polarization does not occur and therefore parabolic CB does not contribute to the anisotropic conductivity $\Delta\sigma = \sigma_{[110]} - \sigma_{[\bar{1}10]}$. However, the VB momentum asymmetry of holes induces the anisotropic conductivity due to the hole effective mass asymmetry, especially for the heavy-hole band [66]. From symmetry considerations, VB asymmetric distribution might also occur in Configuration 1. However, according to previous coherent phonon spectroscopies [26-28], the VB asymmetric distribution is much stronger in Configuration 2. Thus, we assume that CB valley polarization (VB asymmetric distribution) can be probed in Configuration 1 (2), as justified by the following experimental results.

Before discussing the off-diagonal elements, we first address the longitudinal response of photoexcited carriers. Figure 2(a) presents a 2D plot of the detected THz field, $E_x(t_1, t_2)$, obtained using a 900 nm pump wavelength. The THz waveforms $E_x(t_1)$ at fixed pump delays $t_2 = -0.5, 1.0, 3.0$ ps are shown in Fig. 2(b). Figure 2(c) displays a vertical profile of E_x as a function of pump delay t_2 , where the probe delay was fixed at $t_1 = 0$ ps. The pump pulse enters the sample at $t_2 = 0$ ps, altering the probe THz waveform due to the longitudinal response of the photoexcited carriers [37]. The carrier lifetime was significantly longer than the time window of our experiment (~ 100 ps) due to the indirect transition in Si. From the longitudinal optical conductivity spectra $\sigma_{xx}(\omega)$ and the Drude model fitting (See Supplemental Material) [47], the carrier density was evaluated as $4.6 \times 10^{16} \text{ cm}^{-3}$ at most for the 900 nm pump wavelength, which was in the linear regime to the pump fluence. The carrier density further decreased for longer pump wavelengths.

Next, we discuss the polarization rotation of the THz probe field. Figure 2(d) shows the dynamics of the peak of light-induced probe polarization rotation ΔE_y as a function of pump delay t_2 up to 50 ps for a 1000 nm pump wavelength. Immediately after the pump, large polarization rotations of up to 8.0 and 3.1 mrad were observed for Configurations 1 and 2, which rapidly decay within a few ps. This fast relaxation of the transverse response contrasts with the long-lasting longitudinal response shown in Fig. 2(c). In addition, after the fast decay, a slower component of approximately 0.67 mrad is also discerned.

To discuss the fast relaxation signal more closely, the 2D time-domain data $\Delta E_y(t_1, t_2)$ for the 900 nm pump with $0 < t_2 < 4$ ps in Configuration 1 are shown in Fig. 2(e). The simplest approach to analyzing the dynamics is to cut out the vertical profile, namely ΔE_y as a function of the pump delay t_2 with a fixed t_1 , as shown in Fig. 2(c). However, the 2D plot in Fig. 2(e) indicates that: (i) a diagonally oscillating wavy signal appears in the ultrafast regime at $t_2 \sim 0$ ps, and (ii) the vertical signals decaying along t_2 are slightly tilted, suggesting a phase shift in the THz waveform $\Delta E_y(t_1)$. The (almost) vertical signal changing along t_2 is attributed to the anisotropic conductivity of photoexcited carriers in response to the THz probe pulse. By contrast, the diagonally oscillating signal can be attributed to nonlinear photocurrent generation during the temporal overlap of the NIR pump pulse and THz probe field. We refer to this as the field-induced photogalvanic effect, as this process can be regarded as a nominally second-order photocurrent generation by NIR pulses under inversion symmetry breaking by the THz field. A similar result has also been recently observed in THz Faraday spectroscopy for GaAs excited by circularly polarized pump pulses [59]. Although both signals of the anisotropic conductivity and field-induced photogalvanic effect overlap in the time domain, they can be separated in 2D Fourier analysis because of their different dependences on t_1 and t_2 (see Supplemental Material) [47]. Figure 2(f) shows the extracted anisotropic conductivity component $\Delta E_y^{\text{ANI}}(t_1, t_2)$ in the 2D time domain. In addition, the phase of the THz waveform $\Delta E_y^{\text{ANI}}(t_1)$ gradually shifts as the pump delay t_2 passes in Fig. 2(f), which can be attributed to slow thermalization of photoexcited carriers. To eliminate this phase shift and evaluate the information of electron population, we performed the Fourier transformation at each pump delay t_2 . Figure 2(g) shows $|\Delta E_y^{\text{ANI}}(\omega_1, t_2)|$, which represents the time evolution of the anisotropic conductivity signal in the spectral domain. Thus, we are ready to discuss the relaxation dynamics of CB valley polarization. Similarly, the same analysis was conducted for Configuration 2 to discuss the VB momentum asymmetry dynamics.

Figures 3(a) and 3(b) show the time evolutions of the spectral peak $|\Delta E_y^{\text{ANI}}(\omega_1/2\pi = 1.4 \text{ THz})|$ in Configurations 1 and 2, corresponding to the CB valley polarization and VB momentum asymmetry, respectively, for various pump wavelengths. The data were fitted using a single exponential function with an offset (see Supplemental Material) [47] to evaluate the magnitude and decay time of anisotropic conductivity. Figure 3(c) shows the pump photon energy dependence of the signal magnitude for Configurations 1 (CB) and 2 (VB) on the left axis. Additionally, the photoexcited carrier density N_{carr} , evaluated from the Drude model fitting in $\sigma_{xx}(\omega)$, is also plotted on the right axis. N_{carr} increases monotonically as the pump photon energy rises due to the increasing absorption. While the VB momentum asymmetry signal follows a similar trend, the CB valley polarization reaches a maximum around 1.25 eV and then decreases for higher photon energies. According to the band dispersion of electrons in Si [67], the energy band X_1 at the X-point, located just above the CB bottom in the Δ -valley, is involved in optical transitions above 1.25 eV. The result in Fig. 3(c) suggests that the proximity of this band may hinder the optical injection of valley polarization.

Figure 3(d) compares the relaxation times τ for the CB valley polarization (Configuration 1) and VB momentum asymmetry (Configuration 2) as a function of the pump photon energy. The results show distinct relaxation times for Configurations 1 and 2, confirming that the CB and VB contributions were separately observed in our polarization-selective scheme. For any pump photon energy, the CB valley polarization persists for a longer time than the VB momentum asymmetry. We found that the valley relaxation time at the band edge exceeds 1.5 ps even at room temperature, which is 20 times longer than the valley relaxation time in monolayer MoS₂ at room temperature [68]. In previous time-resolved spectroscopies for Si, the electron-phonon scattering of 260 fs for a pump photon energy of 1.55 eV [26] and the L-X valley scattering of 180 fs for two-photon (3.4 eV) excitation [23] were reported. Our work demonstrates that the valley relaxation time can be significantly extended at the band edge due to fewer scattering channels.

Figure 3(e) shows the relaxation rate $\Gamma = 1/\tau$ as a function of the excess energy above the bandgap, compared with the calculated intervalley scattering rate previously reported [34]. The results show a good agreement below the excess energy of ~ 60 meV. In contrast, the calculation exhibits a significant increase above this threshold. This behavior can be explained by considering the differences in the phonon modes involved. As schematically shown in Fig. 3(g), intervalley scattering is classified into g- and f-processes: the g-process involves scattering to the opposite valley on the same axis, mediated by LO phonons, whereas the f-process involves scattering to one of the four valleys in other directions, mediated by LA, TO, and TA phonons [69]. The calculation of the intervalley scattering in Fig. 3(e) includes both g- and f-processes ($\Gamma_g + \Gamma_f$) [34],

whereas our experiment observes the valley relaxation rate corresponding only to the f-process (Γ_f). The dotted line in Fig. 3(e) represents the LO phonon energy, which is approximately 60 meV [60] as shown in Fig. 3(f). The threshold-like increase in the calculation coincides with the LO phonon energy, above which the g-process becomes dominant. Therefore, the results of this work experimentally demonstrate that the intervalley scattering rate at the band edge is dominated by the f-process, leading to a long valley relaxation time >1.5 ps at room temperature.

In conclusion, we experimentally investigated the anisotropic conductivity dynamics of carriers photoinjected at the band edge to study CB valley polarization of electrons and VB momentum asymmetry of holes using time- and polarization-resolved THz spectroscopy. Our results demonstrate that the f-process intervalley scattering time for band-edge carriers exceeds 1.5 ps at room temperature, which is consistent with theoretical calculations and far beyond the previous valleytronics materials. The remarkable robustness of valley degree of freedom in Si will stimulate further investigation for their controllability and readability toward Si-based valleytronics at room temperature. Furthermore, the ultrafast, sensitive, and noncontact detection of anisotropic conductivity based on THz polarimetry techniques can also be applied in variety of materials, which will open a new avenue for multiband semiconductor valleytronics.

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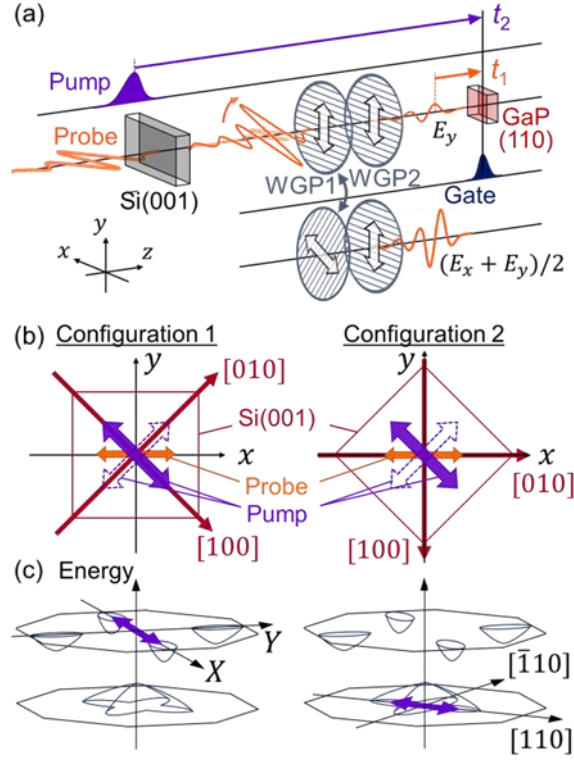


FIG. 1. (a) Schematic of the experiment using the NIR pump (purple), THz probe (orange), and gate (black) pulses. WGP: wire-grid polarizer. WGP1 was rotated to observe E_y and $(E_x + E_y)/2$ separately (see text). (b) Configurations of the pump (purple) and probe (orange) polarization directions relative to the crystalline axes (dark red). The pump direction alternates between the solid and dotted arrows. (c) Schematics illustrating CB valley polarization and VB momentum asymmetry in momentum space.

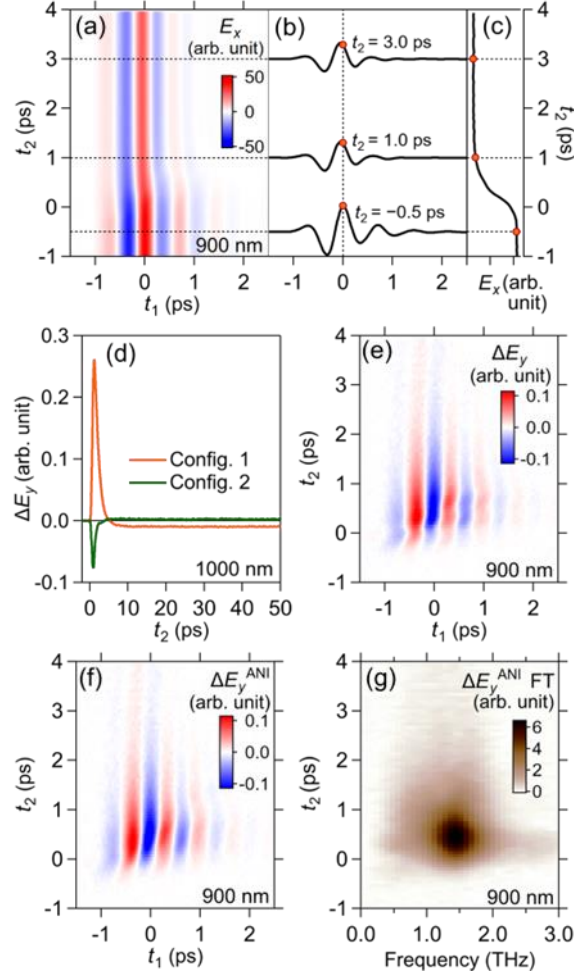


FIG. 2. (a) 2D plot of the transmitted THz probe field E_x as a function of probe delay t_1 and pump delay t_2 for a 900 nm pump. (b) Waveforms of $E_x(t_1)$ at fixed pump delays. (c) Vertical profile of $E_x(t_2)$ at a fixed probe delay $t_1=0$ ps. (d) Dynamics of light-induced polarization rotation ΔE_y as a function of the pump delay t_2 with a fixed probe delay. The orange and green curves correspond to Configuration 1 and 2, respectively. (e) 2D plot of $\Delta E_y(t_1, t_2)$ with the pump at 900 nm. (f) 2D plot of anisotropic conductivity signal $\Delta E_y^{\text{ANI}}(t_1, t_2)$. (g) Fourier transform of (f) at each delay t_2 .

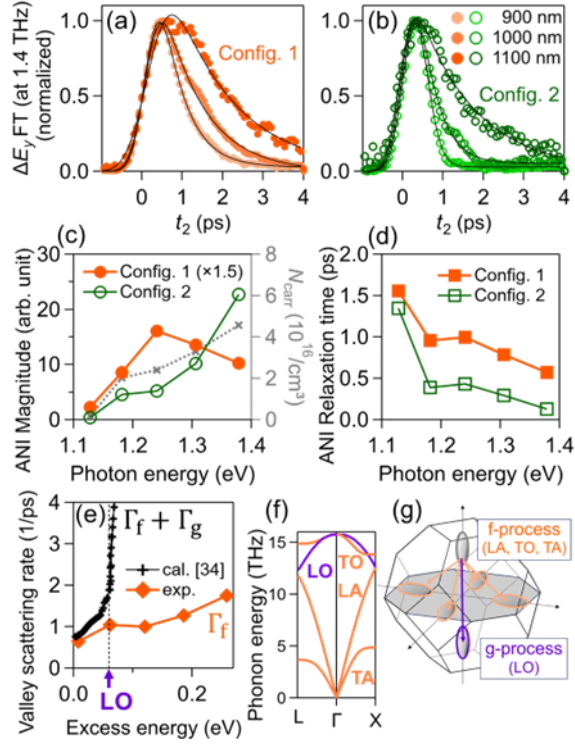


FIG. 3. (a)(b) ΔE_y at the probe frequency $\omega_1/2\pi=1.4$ THz as a function of pump delay t_2 in Configs. 1 and 2, respectively, for various pump wavelengths. The black solid curves are the fitting results. (c) Magnitude of the anisotropic conductivity (left axis) for CB and VB as a function of the pump photon energy. The right axis shows the photoexcited carrier density. (d) The relaxation time of CB valley polarization and VB momentum asymmetry as a function of the pump photon energy. (e) The scattering rate vs the excess energy from the band gap for the fitting results of this experiment and the previous calculation [34]. (f) The phonon dispersion relation in Si. (g) Schematics of intervalley scattering by phonons with g- and f-processes.

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